

SEMICONDUCTOR STRUCTURE AND METHOD FOR FORMING SEMICONDUCTOR STRUCTURE

ABSTRACT

The embodiments of the disclosure provide a semiconductor structure and a method for forming a semiconductor structure. The method for forming the semiconductor structure includes the following operations. A base is provided, in which the base includes a substrate, a first semiconductor layer and a second semiconductor layer sequentially formed on one another. A plurality of first isolation structures spaced apart from each other and a plurality of second isolation structures spaced apart from each other are formed in the base, in which a source layer formed in the second semiconductor layer and a drain layer formed in the substrate are provided between any two adjacent first isolation structures of the plurality of first isolation structures, each of the plurality of first isolation structures extends in a first direction, and each of the plurality of second isolation structures extends in a second direction. A channel layer is formed in the first semiconductor layer, in which a through hole extending in a same direction as the first direction is provided between the channel layer and each of two first isolation structures adjacent to the channel layer. A gate structure is formed in the through hole.

[Fig 1A]